## Problem 5 Semiconductor Materials

- 1. A 100 mW laser beam with wavelength  $\lambda = 6328$  Å is focused onto a GaAs sample that is 0.5  $\mu$ m thick. The absorption coefficient at this wavelength is  $3 \times 10^4$  cm<sup>-1</sup>, the bandgap is  $E_g = 1.42$  eV at 300 K, and  $m_e^* = 0.067$   $m_o$ .
  - a) Find the number of photons emitted per second by radiative recombination in the GaAs, assuming perfect quantum efficiency.
  - b) What is the power delivered to the sample as heat?
- 2. An aluminum layer having the work function  $q\phi_m = 4.1 \text{ eV}$  is deposited onto a SiC substrate. SiC has an electron affinity of 3.9 eV and a bandgap of 3.0 eV and its effective density of states at room temperature of  $N_C = N_V = 2.51 \times 10^{19} \text{ cm}^{-3}$ . Determine the doping type and level so that the work function of the SiC matches the Al layer at room temperature.

The fraction of incidence power absorbed is f=1-e when ~ is absorpt could and L = thickness. Here f= 1-exp (-3×104. 0.5×104)= 0.777 The energy of an incident photon is  $E_{ph} = h \stackrel{c}{,} = \frac{6.63 \times 10^{-34} \times 3 \times 10^{6}}{632.6 \times 10^{-9}} = 3.14 \times 10^{-9} \text{ J}$  = 1.96 eV=)  $\# photom f_{s} a b sin bul is$ =  $\frac{f}{f} \cdot 100 \times 10^{-3} = 2.47 \times 10^{-7} photom f_{s}$ 



<i>a</i>	$1.6 \times 10^{-19}$ C
Ч	$1.0 \times 10^{-14} \text{ E}$
$\epsilon_{o}$	$8.85 \times 10^{-11} \text{ F/cm}$
$K_s$	11.8 (Si)
Ko	3.9 (SiO <sub>2</sub> )
$k_B$	$8.617 \times 10^{-5} \text{ eV/K}$
h	$6.63  imes 10^{-34} \text{ J} \text{ s}$
$m_o$	$9.11  imes 10^{-31}  m kg$
$k_BT/q$	0.0259 V at 300 K
С	$3 \times 10^8 \text{ m/s}$

electron charge permittivity of free space relative dielectric constant relative dielectric constant Boltzman's constant Planck constant electron mass thermal voltage speed of light

Each excited electron falls back down to C.B. edge (giving of heat) and then with whity quantum afficiency emits a photon. => # pl emitted = 2.47 ×10 ph 5 The best generated is this number  $\chi = p_1 - E_q = 0.54 \text{ eV}$ Heat = 2.47×10 × 0.54 × 1.6×10 J/s Heat = 21.5 mW e 7 = 3.9 2 . 4.1 3.0 2 EF close to CB => n-type · n= Nce (EF-EC)/ET 19 -0.2/.0259 = 2,51×10 × e = 8.15×10 m<sup>-3</sup>